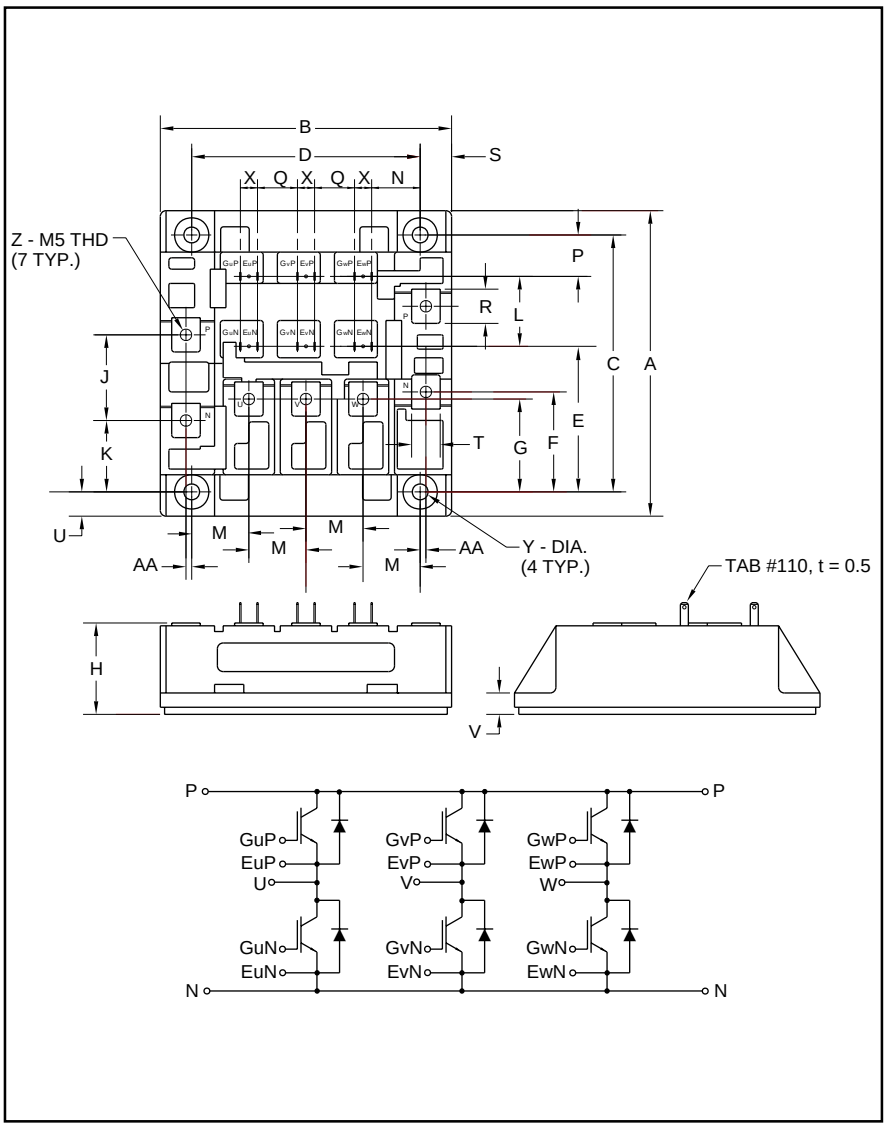
MITSUBISHI IGBT MODULES

CM150TF-12H

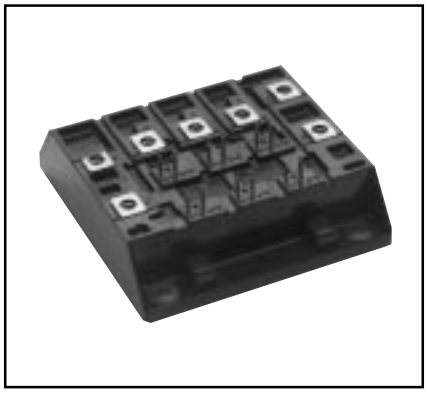
HIGH POWER SWITCHING USE
INSULATED TYPE



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.21	107.0
B	4.02	102.0
C	3.543±0.01	90.0±0.25
D	3.15±0.01	80.0±0.25
E	2.01	51.0
F	1.38	35.0
G	1.28	32.5
H	1.26 Max.	32.0 Max
J	1.18	30.0
K	0.98	25.0
L	0.96	24.5
M	0.79	20.0
N	0.67	17.0

Dimensions	Inches	Millimeters
P	0.57	14.5
Q	0.55	14.0
R	0.47	12.0
S	0.43	11.0
T	0.39	10.0
U	0.33	8.5
V	0.30	7.5
X	0.24	6.0
Y	0.22	5.5
Z	M5 Metric	M5
AA	0.08	2.0



Description:
Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of six IGBTs in a three phase bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:
- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ High Frequency Operation
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:
- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies

Ordering Information:
Example: Select the complete part module number you desire from the table below -i.e. CM150TF-12H is a 600V (V_{CES}), 150 Ampere Six-IGBT Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	150	12

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Absolute Maximum Ratings, T_j = 25 °C unless otherwise specified

Ratings	Symbol	CM150TF-12H	Units
Junction Temperature	T_j	–40 to 150	°C
Storage Temperature	T_{stg}	–40 to 125	°C
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	600	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	±20	Volts
Collector Current (T_C = 25°C)	I_C	150	Amperes
Peak Collector Current	I_{CM}	300*	Amperes
Emitter Current** (T_C = 25°C)	I_R	150	Amperes
Peak Emitter Current**	I_{EM}	300*	Amperes
Maximum Collector Dissipation (T_C = 25°C, $T_j \leq$ 150°C)	P_c	600	Watts
Mounting Torque, M5 Main Terminal	–	1.47 ~ 1.96	N · m
Mounting Torque, M5 Mounting	–	1.47 ~ 1.96	N · m
Weight	–	830	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{iso}	2500	Vrms

*Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.
**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics, T_j = 25 °C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}$, V_{GE} = 0V	–	–	1.0	mA
Gate Leakage Current	I_{GES}	$V_{GE} = V_{GES}$, V_{CE} = 0V	–	–	0.5	µA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	I_C = 15mA, V_{CE} = 10V	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 150A, V_{GE} = 15V	–	2.1	2.8**	Volts
		I_C = 150A, V_{GE} = 15V, T_j = 150°C	–	2.15	–	Volts
Total Gate Charge	Q_G	V_{CC} = 300V, I_C = 150A, V_{GE} = 15V	–	450	–	nC
Emitter-Collector Voltage	V_{EC}	I_E = 150A, V_{GE} = 0V	–	–	2.8	Volts

** Pulse width and repetition rate should be such that device junction temperature rise is negligible.

Dynamic Electrical Characteristics, T_j = 25 °C unless otherwise specified

Characteristics		Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance		C_{ies}	V_{GE} = 0V, V_{CE} = 10V	–	–	15	nF
Output Capacitance		C_{oes}		–	–	5.3	nF
Reverse Transfer Capacitance		C_{res}		–	–	3	nF
Resistive	Turn-on Delay Time	$t_{d(on)}$	V_{CC} = 300V, I_C = 150A, $V_{GE1} = V_{GE2}$ = 15V, R_G = 4.2Ω	–	–	200	ns
Load	Rise Time	t_r		–	–	550	ns
Switching	Turn-off Delay Time	$t_{d(off)}$		–	–	300	ns
Times	Fall Time	t_f		–	–	300	ns
Diode Reverse Recovery Time		t_{rr}	I_E = 150A, di_E/dt = –300A/µs	–	–	110	ns
Diode Reverse Recovery Charge		Q_{rr}	I_E = 150A, di_E/dt = –300A/µs	–	0.41	–	µC

Thermal and Mechanical Characteristics, T_j = 25 °C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per IGBT	–	–	0.21	°C/W
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per FWDi	–	–	0.47	°C/W
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	–	–	0.025	°C/W

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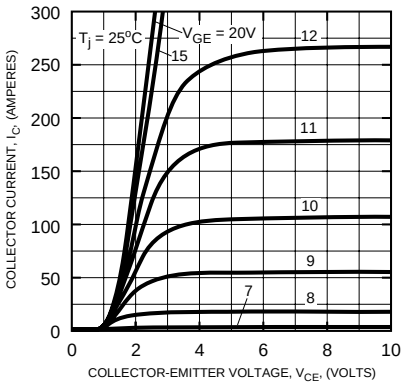
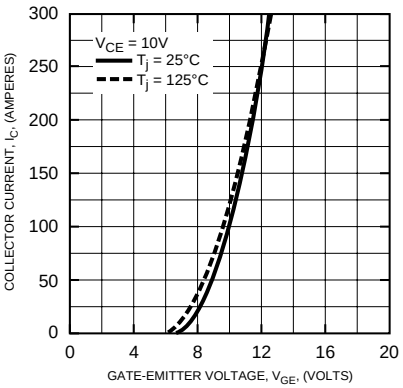
INSULATED TYPE

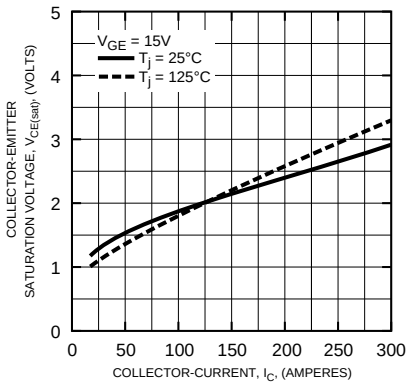
OUTPUT CHARACTERISTICS (TYPICAL)



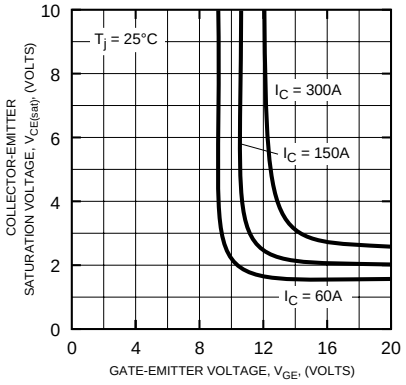
TRANSFER CHARACTERISTICS (TYPICAL)



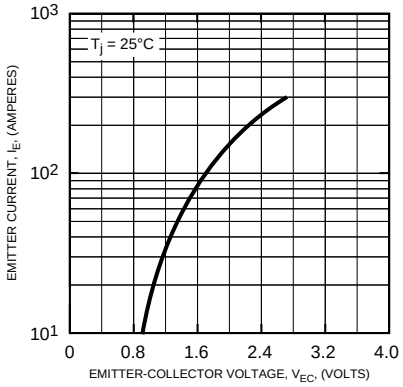
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



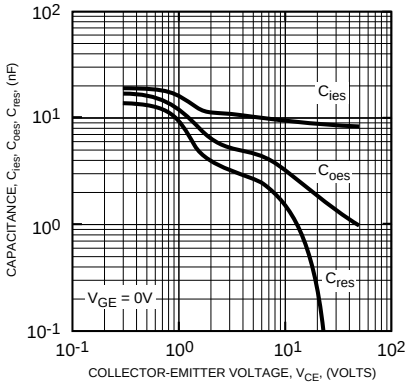
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



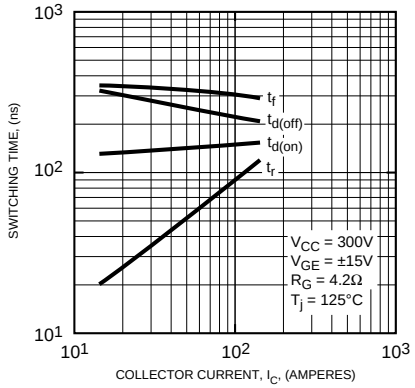
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



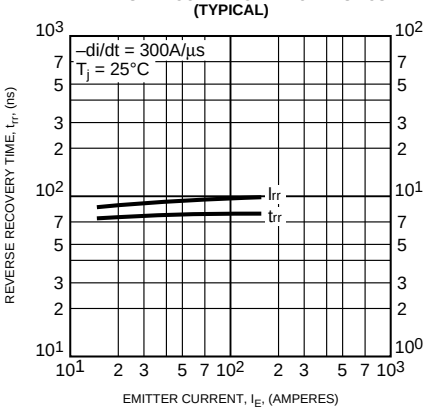
CAPACITANCE VS. V_{CE} (TYPICAL)



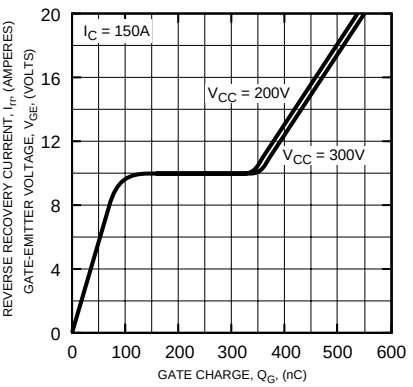
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



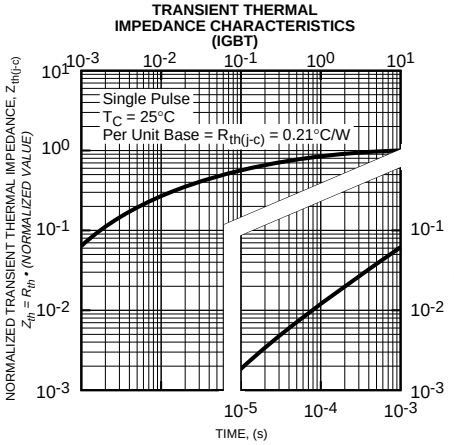
REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

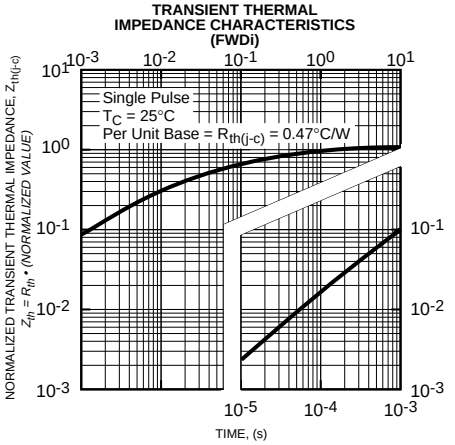


GATE CHARGE, V_{GE}



MITSUBISHI ELECTRIC


TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(IGBT)
NORMALIZED TRANSIENT THERMAL IMPEDANCE, Zth(j-c)
Zth = Rth • (NORMALIZED VALUE)
Single Pulse
TC = 25°C
Per Unit Base = Rth(j-c) = 0.21°C/W
TIME, (s)


TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(FWDi)
NORMALIZED TRANSIENT THERMAL IMPEDANCE, Zth(j-c)
Zth = Rth • (NORMALIZED VALUE)
Single Pulse
TC = 25°C
Per Unit Base = Rth(j-c) = 0.47°C/W
TIME, (s)